NTST30120CT, NTSJ30120CTG, NTSB30120CT-1G, NTSB30120CTG, NTSB30120CTT4G

### Very Low Forward Voltage Trench-based Schottky Rectifier

Exceptionally Low  $V_F = 0.50 \text{ V}$  at  $I_F = 5 \text{ A}$ 

#### **Features**

- Fine Lithography Trench-based Schottky Technology for Very Low Forward Voltage and Low Leakage
- Fast Switching with Exceptional Temperature Stability
- Low Power Loss and Lower Operating Temperature
- Higher Efficiency for Achieving Regulatory Compliance
- Low Thermal Resistance
- High Surge Capability
- These are Pb-Free Devices

#### **Typical Applications**

- Switching Power Supplies including Notebook / Netbook Adapters, ATX and Flat Panel Display
- High Frequency and DC-DC Converters
- Freewheeling and OR-ing diodes
- Reverse Battery Protection
- Instrumentation

#### **Mechanical Characteristics**

- Case: Epoxy, Molded
- Epoxy Meets Flammability Rating UL 94-0 @ 0.125 in
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Maximum for 10 sec

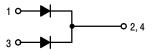


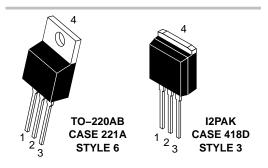
ON Semiconductor®

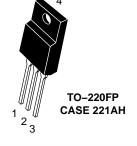
www.onsemi.com

VERY LOW FORWARD VOLT-AGE, LOW LEAKAGE SCHOT-TKY BARRIER RECTIFIERS 30 AMPERES, 120 VOLTS

#### **PIN CONNECTIONS**









#### ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

#### NTST30120CT, NTSJ30120CTG, NTSB30120CT-1G, NTSB30120CTG, NTSB30120CTT4G

#### **MAXIMUM RATINGS**

Rating		Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage		V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	120	V
Average Rectified Forward Current (Rated V <sub>R</sub> , T <sub>C</sub> = 125°C)	Per device Per diode	I <sub>F(AV)</sub>	30 15	A
Peak Repetitive Forward Current (Rated V <sub>R</sub> , Square Wave, 20 kHz, T <sub>C</sub> = 130°C)	Per device Per diode	I <sub>FRM</sub>	60 30	A
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)		I <sub>FSM</sub>	150	А
Operating Junction Temperature		TJ	-40 to +150	°C
Storage Temperature		T <sub>stg</sub>	-40 to +150	°C
Voltage Rate of Change (Rated V <sub>R</sub> )		dv/dt	10,000	V/µs

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### THERMAL CHARACTERISTICS

Rating	Symbol	NTST30120CTG NTSB30120CT-1G	NTSB30120CTG	NTSJ30120CTG	Unit
Maximum Thermal Resistance per Diode Junction-to-Case Junction-to-Ambient	$R_{ heta JC} \ R_{ heta JA}$	2.5 70	1.14 46.6	4.05 105	°C/W

#### **ELECTRICAL CHARACTERISTICS** (Per Leg unless otherwise noted)

Rating	Symbol	Тур	Max	Unit
Maximum Instantaneous Forward Voltage (Note 1)	V <sub>F</sub>			V
$(I_F = 5 \text{ A}, T_J = 25^{\circ}\text{C})$		0.56	_	
$(I_F = 7.5 \text{ A}, T_J = 25^{\circ}\text{C})$		0.71	_	
$(I_F = 15 \text{ A}, T_J = 25^{\circ}\text{C})$		0.90	1.08	
$(I_F = 5 \text{ A}, T_A = 125^{\circ}\text{C})$		0.50	_	
$(I_F = 7.5 \text{ A}, T_J = 125^{\circ}\text{C})$		0.60	_	
(I <sub>F</sub> = 15 A, T <sub>J</sub> = 125°C)		0.68	0.76	
Maximum Instantaneous Reverse Current (Note 1)	I <sub>R</sub>			
$(V_R = 90 \text{ V}, T_J = 25^{\circ}\text{C})$		16	_	μΑ
$(V_R = 90 \text{ V}, T_J = 125^{\circ}\text{C})$		11	_	mA
(Rated dc Voltage, T <sub>J</sub> = 25°C)		_	800	μΑ
(Rated dc Voltage, T <sub>J</sub> = 125°C)		25	100	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 1. Pulse Test: Pulse Width =  $300 \,\mu s$ , Duty Cycle  $\leq 2.0\%$ 

#### NTST30120CT, NTSJ30120CTG, NTSB30120CT-1G, NTSB30120CTG, NTSB30120CTT4G

#### **TYPICAL CHARACTERISITICS**

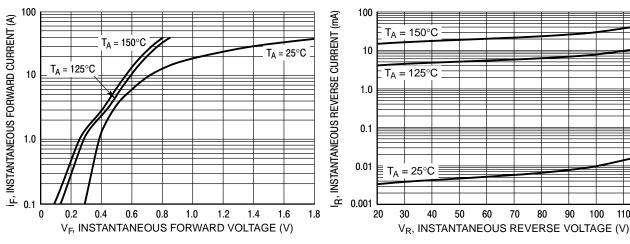
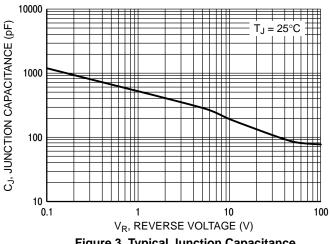


Figure 1. Typical Instantaneous Forward Characteristics

**Figure 2. Typical Reverse Current** Characteristics

110

120



**Figure 3. Typical Junction Capacitance** 

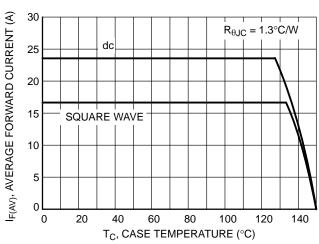
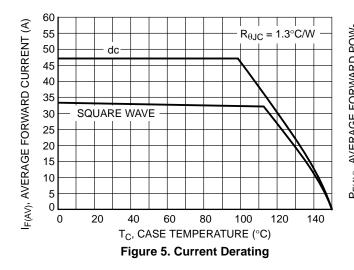


Figure 4. Current Derating per Leg



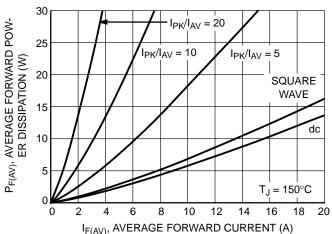


Figure 6. Forward Power Dissipation

# NTST30120CT, NTSJ30120CTG, NTSB30120CT-1G, NTSB30120CTG, NTSB30120CTT4G

#### **TYPICAL CHARACTERISITICS**

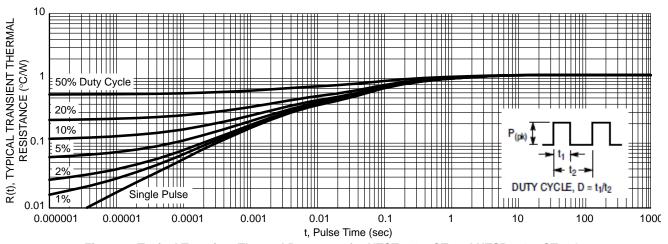


Figure 7. Typical Transient Thermal Response for NTST30120CT and NTSB30120CT-1G

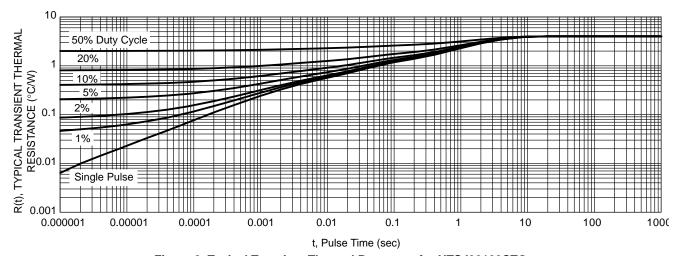


Figure 8. Typical Transient Thermal Response for NTSJ30120CTG

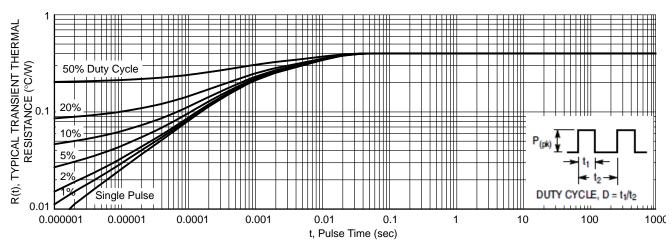


Figure 9. Typical Transient Thermal Response for NTSB30120CTG

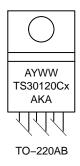
# NTST30120CT, NTSJ30120CTG, NTSB30120CT-1G, NTSB30120CTG, NTSB30120CTT4G

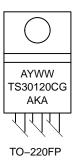
#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
NTST30120CTG	TO-220AB (Pb-Free)	50 Units / Rail
NTSJ30120CTG	TO-220FP (Halide-Free)	50 Units / Rail
NTSB30120CT-1G	I <sup>2</sup> PAK (Pb-Free)	50 Units / Rail
NTSB30120CTG	D <sup>2</sup> PAK (Pb-Free)	50 Units / Rail
NTSB30120CTT4G	D <sup>2</sup> PAK (Pb-Free)	800 / Tape & Reel

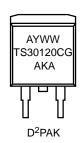
<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### **MARKING DIAGRAMS**









A = Assembly Location

Y = Year

WW = Work Week
AKA = Polarity Designator

x = G or H

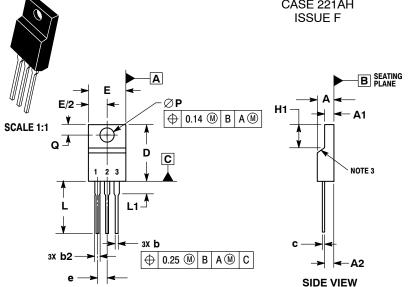
G = Pb-Free Package

H = Halide-Free Package



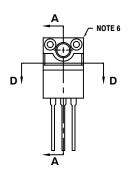
### TO-220 FULLPACK, 3-LEAD CASE 221AH

**DATE 30 SEP 2014** 





**FRONT VIEW** 





NOTE 6

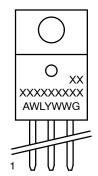
**SECTION A-A** 

**ALTERNATE CONSTRUCTION** 

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS.
  3. CONTOUR UNCONTROLLED IN THIS AREA.
- CONTOUR ONCOUNTIOLLED IN THIS AREA
   DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH AND GATE
   PROTRUSIONS. MOLD FLASH AND GATE PROTRUSIONS NOT TO
   EXCEED 0.13 PER SIDE. THESE DIMENSIONS ARE TO BE MEA SURED AT OUTERMOST EXTREME OF THE PLASTIC BODY.
   DIMENSION b2 DOES NOT INCLUDE DAMBAR PROTRUSION.
   LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 2.00.
- CONTOURS AND FEATURES OF THE MOLDED PACKAGE BODY MAY VARY WITHIN THE ENVELOP DEFINED BY DIMENSIONS AT AND H1 FOR MANUFACTURING PURPOSES.

	MILLIMETERS			
DIM	MIN	MAX		
Α	4.30	4.70		
A1	2.50	2.90		
A2	2.50	2.90		
b	0.54	0.84		
b2	1.10	1.40		
C	0.49	0.79		
D	14.70	15.30		
Е	9.70	10.30		
е	2.54	BSC		
H1	6.60	7.10		
L	12.50	14.73		
L1		2.80		
P	3.00	3.40		
Q	2.80	3.20		

#### **GENERIC MARKING DIAGRAM\***



= Assembly Location

WL = Wafer Lot

= Year

WW = Work Week

G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1:		STYLE 2:	
PIN 1.	MAIN TERMINAL 1	PIN 1.	CATHODE
2.	MAIN TERMINAL 2	2.	ANODE
3.	GATE	3.	GATE

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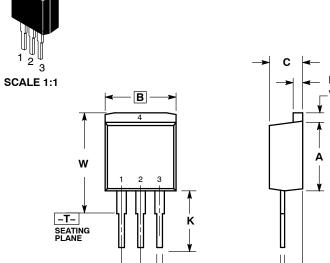




#### D2PAK, 3-LEAD, STRAIGHT

**CASE 418 ISSUE J** 

**DATE 08 OCT 2003** 



STYLE 1:

PIN 1. BASE 2. COLLECTOR

3. EMITTER 4. COLLECTOR

STYLE 2: PIN 1. GATE 2. DRAIN

G

3. SOURCE 4. DRAIN

D 3 PL

⊕ 0.13 (0.005) M T B M

PIN 1. ANODE 2. CATHODE 3. ANODE 4. CATHODE

STYLE 3:

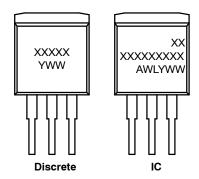
STYLE 4: PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH. 3. 418-01 THRU -04 OBSOLETE, NEW STANDARD 418-05.

	INC	HES	MILLIM	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.340	0.380	8.64	9.65
В	0.380	0.405	9.65	10.29
С	0.160	0.190	4.06	4.83
D	0.020	0.035	0.51	0.89
E	0.045	0.055	1.14	1.40
G	0.100	BSC	2.54	BSC
Н	0.080	0.110	2.03	2.79
J	0.018	0.025	0.46	0.64
K	0.285	0.305	7.493	7.747
V	0.045	0.055	1.14	1.40
w	0.525	0.545	13 335	13 8/3

#### **GENERIC MARKING DIAGRAMS\***



XXXX = Specific Device Code = Assembly Location Α

= Wafer Lot WL Υ = Year ww = Work Week

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

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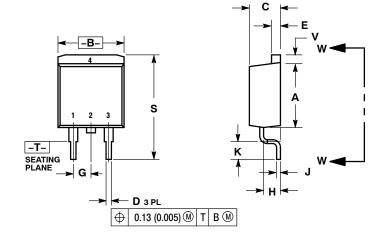




D<sup>2</sup>PAK 3 CASE 418B-04 **ISSUE L** 

**DATE 17 FEB 2015** 

#### SCALE 1:1



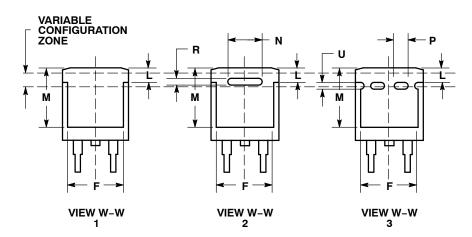
- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
   CONTROLLING DIMENSION: INCH.
- 3. 418B-01 THRU 418B-03 OBSOLETE,

NEW STANDARD 418B-04.

INCHES		MILLIMETERS	
MIN	MAX	MIN	MAX
0.340	0.380	8.64	9.65
0.380	0.405	9.65	10.29
0.160	0.190	4.06	4.83
0.020	0.035	0.51	0.89
0.045	0.055	1.14	1.40
0.310	0.350	7.87	8.89
0.100 BSC		2.54 BSC	
0.080	0.110	2.03	2.79
0.018	0.025	0.46	0.64
0.090	0.110	2.29	2.79
0.052	0.072	1.32	1.83
0.280	0.320	7.11	8.13
0.197	REF	5.00	REF
0.079	REF	2.00	REF
0.039	REF	0.99	REF
	MIN 0.340 0.380 0.160 0.020 0.045 0.310 0.100 0.080 0.018 0.090 0.052 0.280 0.197	MIN         MAX           0.340         0.380           0.380         0.405           0.160         0.190           0.020         0.035           0.341         0.350           0.100         BSC           0.080         0.110           0.010         0.090           0.090         0.110           0.052         0.072	MIN         MAX         MIN           0.340         0.380         8.64           0.380         0.405         9.65           0.160         0.190         4.06           0.020         0.035         0.51           0.045         0.055         1.14           0.310         0.350         7.87           0.100         BSC         2.54           0.080         0.110         2.03           0.018         0.025         0.46           0.090         0.110         2.29           0.052         0.072         1.32           0.280         0.320         7.11           0.197         REF         5.00           0.079         REF         2.00

 S
 0.575
 0.625
 14.60
 15.88

 V
 0.045
 0.055
 1.14
 1.40



STYLE 1: PIN 1. BASE 2. COLLECTOR
3. EMITTER
4. COLLECTOR STYLE 2: PIN 1. GATE 2. DRAIN 3. SOURCE 4. DRAIN STYLE 3: PIN 1. ANODE 2. CATHODE 3. ANODE 4. CATHODE

STYLE 4:

PIN 1. GATE 2. COLLECTOR 3. EMITTER 4. COLLECTOR STYLE 5: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. ANODE

STYLE 6: PIN 1. NO CONNECT 2. CATHODE 3. ANODE 4. CATHODE

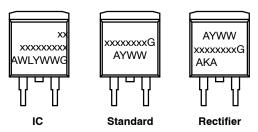
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**DATE 17 FEB 2015** 

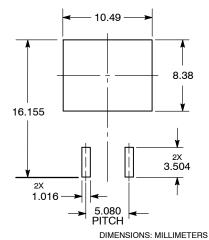
# GENERIC MARKING DIAGRAM\*



xx = Specific Device Code A = Assembly Location

WL = Wafer Lot
Y = Year
WW = Work Week
G = Pb-Free Package
AKA = Polarity Indicator

#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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